

REMARKS

Claims 1-9 are pending in the application.

In the attached form PTO-1449, the Examiner has crossed out the listed references because copies of these references were not provided. A Supplemental Information Disclosure Statement, including copies of these references, is being filed with this response.

Claims 1, 2, 4 and 8 have been rejected under 35 USC 102(e) as being anticipated by Wollesen (U.S. Patent No. 6,020,222). This rejection is respectfully traversed.

Claim 1 recites an SRAM comprising MOS transistors, each including "a channel-forming semiconductor region and a gate electrically connected with each other."

The Examiner asserts that Wollesen teaches SOI devices which have DTMOS devices and can be used as an SRAM with a resistor. The Examiner asserts that these devices can function as a DTMOS device or be biased to a voltage.

In FIGS. 1 and 2, Wollesen discloses an SOI device having transistors Q1 and Q2. These transistors are not DTMOS transistors. In FIG. 3, Wollesen discloses an SOI N-channel DTMOS. Wollesen discloses that a P channel DTMOS can be constructed by reversing the dopant types of the device shown in FIG. 3 (col. 7, lines 8-10). In FIG. 12, Wollesen discloses an SRAM cell including floating body SOI transistors Q1 and Q2 and linked body transistors Q3 and Q4. As stated in column 9, lines 8-11, the floating body transistors Q1 and Q2 can be established by the N channel floating body transistor Q1 shown in FIGS. 1 and 2. Wollesen does not, however, disclose that a DTMOS can be used for any of the transistors in the device disclosed in FIG. 12. Merely disclosing the structure of a DTMOS device, which was well known in the art at the time of the invention, is insufficient to support this rejection. There is simply nothing in Wollesen which suggests using a DTMOS device for any of the transistors Q1-

Q4 of the device disclosed in FIG. 12. Accordingly, the features of claim 1 are neither taught nor suggested by Wollesen.

Claims 2, 4 and 8 are allowable at least due to their dependency, directly or otherwise, from claim 1. Accordingly, applicant respectfully requests that this rejection be withdrawn.

Claims 5-7 and 9 are rejected under 35 USC 103(a) as being unpatentable over Wollesen. This rejection is respectfully traversed.

Claims 5-7 are allowable at least due to their dependency, directly or otherwise, from claim 1.

Claim 9 recites first MOS transistors which each have a channel-forming semiconductor region formed of a first well and second MOS transistors which each have a channel-forming semiconductor region formed of a second well deeper than the first well. This feature is also recited in claim 4.

Although the Examiner has not specifically commented on the rejection of claim 9, in the rejection of claim 4 the Examiner stated that Wollesen teaches a well 22 which is deeper than the well 16 but opposite types could be used which would reverse the relative values. The Examiner apparently considers that the field oxide layer 16 disclosed in Wollesen is a well for forming a channel-forming semiconductor region. However, the field oxide layer 16 is actually a layer for forming source and drain regions, not a well for forming a channel-forming semiconductor region as asserted by the Examiner. Further, FIG. 1 of Wollesen clearly shows that the wells for N-channel transistors Q1 and Q2 have the same depth as the wells for P-channel transistors Q3 and Q4. Thus, the features of claim 9 are neither disclosed nor suggested by Wollesen. Accordingly, applicant requests that this rejection be withdrawn.

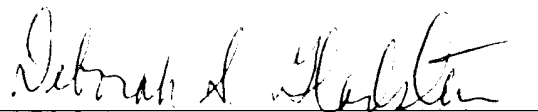
Claim 3 was rejected under 35 USC 103(a) as being unpatentable over Wollesen in view of Tsui (U.S. Patent No. 5,960,289). Claim 3 is allowable at least due to its indirect dependency from claim 1. Accordingly, applicant requests that this rejection be withdrawn.

In the event that the transmittal letter is separated from this document and the Patent and Trademark Office determines that an extension and/or other relief is required, applicant petitions for any required relief including extensions of time and authorizes the Commissioner to charge the cost of such petitions and/or other fees due in connection with the filing of this document to Deposit Account No. 03-1952 referencing docket no. 204552016500.

Respectfully submitted,

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